

Drafts
Pending
Active
L8: (91) (ferroelectric adj2 memory) and (non-saturatS3 nonsaturatS3)
Failed
Saved
(207) (mfs MPMIS) with (ferroelectric ferro-electric)
(109) ((mfs MPMIS) with (ferroelectric ferro-electric)) and (writS
(12) (((mfs MPMIS) with (ferroelectric ferro-electric)) and (writS
(14498) (mfs MPMIS) (metal adj4 (ferroelectric ferro-electric) adj
(3093) ((mfs MPMIS) (metal adj4 (ferroelectric ferro-electric) adj
(29) (((mfs MPMIS) (metal adj4 (ferroelectric ferro-electric) adj4
(18496) (mfs MPMIS) (metal adj3 (ferroelectric ferro-electric
(3302) ((mfs MPMIS) (metal adj3 (ferroelectric ferro-electric
(29) (((mfs MPMIS) (metal adj3 (ferroelectric ferro-electric)
(10) (((mfs MPMIS) (metal adj3 (ferroelectric ferro-electric)
(10) (((mfs MPMIS) (metal adj3 (ferroelectric ferro-electric
(4) ((mfs MPMIS) (metal adj3 (ferroelectric ferro-electric)
(205) ((ferroelectric adj3 capacitor) with (gate adj3 electrode))
(40) (((ferroelectric adj3 capacitor) with (gate adj3 electrode)))
(32) (((ferroelectric adj3 capacitor) with (gate adj3 electrode))
(16) (((ferroelectric adj3 capacitor) with (gate adj3 electrode))
(5690) readS3 same ((voltage potential bias) with drain with sourc
(574) ((unsaturatS3 non-saturatS3) near3 region) and (saturatS3 ne
(22) (((unsaturatS3 non-saturatS3) near3 region) and (saturatS3 ne
(2835) (readS3 same ((voltage potential bias) with drain with sour
(5) (((unsaturatS3 non-saturatS3) near3 region) and (saturatS3 ne
(124614) ((MFS MPMIS ferroelectric) near3 transistor) PerAM non-vo
(22) (((unsaturatS3 non-saturatS3) near3 region) and (saturatS3 ne
(1) (((unsaturatS3 non-saturatS3) near3 region) and (saturatS3 ne

DB: [USPAT.US:PGPUB:EPO:JPO:DERVENT:IBM:TOB]

Detail operator: DR

P: [Date]

Highlight all comments

((ferroelectric and memory) and ((readS3 with ((linear adj2 region)
nonsaturatS3 unsaturatS3 (non adj saturatS3) (un adj saturatS3)))

U	1	Document ID	Issue Date	Pages	Title	Current OR	Current IRef	Retrieval C	Inventor	S	C	P	X	S	S
8	<input type="checkbox"/>	US 6449183 B1	20020910	28	Ferroelectric memory system and method of driving the	365/145	365/149; 365/189.09;		Hirano, Hiroshige et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
9	<input type="checkbox"/>	US 6303270 B1	20011016	15	Highly plasma etch-resistant photoresist composition	430/284.1	430/285.1; 430/287.1;		Flaim, Tony D. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
10	<input type="checkbox"/>	US 6303231 B1	20011016	23	Coating solutions for use in forming bismuth-based	106/470	106/1.12; 106/1.27;		Sawada, Yoshihiro et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
11	<input type="checkbox"/>	US 6197102 B1	20010306	24	Coating solutions for use in forming bismuth-based	106/287.18	106/287.19; 252/62.9PZ;		Sawada, Yoshihiro et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
12	<input type="checkbox"/>	US 6157563 A	20001205	28	Ferroelectric memory system and method of driving the	365/145	365/149		Hirano, Hiroshige et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
13	<input type="checkbox"/>	US 6120912 A	20000919	21	Coating solutions for use in forming bismuth-based	106/470	106/1.05; 257/E21.272;		Sawada, Yoshihiro et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
14	<input type="checkbox"/>	US 5972096 A	19991026	20	Coating solutions for use in forming bismuth-based	106/287.18	106/287.19; 252/62.9PZ;		Sawada, Yoshihiro et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
15	<input type="checkbox"/>	US 5811153 A	19980922	17	Coating solutions for use in forming bismuth-based	427/58	106/1.12; 106/1.25;		Hashimoto, Akira et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
16	<input type="checkbox"/>	US 5696384 A	19971209	13	Composition for formation of electrode pattern	252/182.12	252/182.3; 257/E21.174;		Ogi, Katsumi et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>